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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/444,819	11/22/1999	SHUICHI KIKUCHI	10417-006001	9133

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EXAMINER

RAO, SHRINIVAS H

ART UNIT PAPER NUMBER

2814

DATE MAILED: 06/17/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

09/444,819

Applicant(s)

KIKUCHI ET AL.

Examiner

Steven H. Rao

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 11 April 2003.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-4,8-10,17, 19-32 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☐ Claim(s) 1-4,8-10,17 and 19-32 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on _____ is: a) ☐ approved b) ☐ disapproved by the Examiner.
If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. §§ 119 and 120

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
* See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Attachment(s)

- 1) ☐ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449) Paper No(s) _____
- 4) ☐ Interview Summary (PTO-413) Paper No(s). _____
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: _____

DETAILED ACTION

Applicants' amendment filed on April 11, 2003 has been entered on April 22, 2003.

Therefore claims 1,2 -10 as amended by the amendment 20-32 presently newly added and claims 17 and 19 as previously recited are currently pending in the Application.

Claims 5-7,11-16 and 18 were previously cancelled.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The changes made to 35 U.S.C. 102(e) by the American Inventors Protection Act of 1999 (AIPA) do not apply to the examination of this application as the application being examined was not (1) filed on or after November 29, 2000, or (2) voluntarily published under 35 U.S.C. 122(b). Therefore, this application is examined under 35 U.S.C. 102(e) prior to the amendment by the AIPA (pre-AIPA 35 U.S.C. 102(e)).

Claims 1-2, 8 and 19 are rejected under 35 U.S.C. 102(e) as being anticipated by Kwon et al. (U.S. Patent No. 5,907,173 herein after Kwon)

With respect to claim1 Kwon describes a semiconductor device including : a source region (Kwon fig. 4 # 45, col. 5 line 41), a channel region (Kwon fig.4 # area below gate 44), a drain region (fig.4 # 47, col. 5 line 43), a gate electrode disposed above the channel region (fig. 4 #44, col. 5 line 44), and a drift region disposed

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adjacent to the channel region and extending to and below the drain region (Fig.4 # 43), and wherein the drift region is formed shallowly at least below the gate electrode but formed deeply in a neighborhood of the drain region. (fig. 4 # 43).

With respect to claim 2, Kwon describes a semiconductor device including :

A first conductivity type well region formed in a first conductivity type semiconductor substrate (Kwon fig. 1 p-well), a gate electrode formed on the substrate via a gate insulating film (Fig.1 # 4-a gate electrode and # 32 gate insulating film), a first conductivity type body region (fig. 1 # 6) formed adjacent to the gate electrode , a second conductivity type source region (fig. 1 # 5) and a channel region formed in the first conductivity body region (fig.1 region below gate 4), a second conductivity type drain region formed at a position remote from the first conductivity type body region. (fig.1 # 7) and a second conductivity type drift region formed shallowly from the channel region to the drain region, at least below the gate electrode and formed deeply in a neighborhood of the drain region. (Kwon fig.1).

With respect to claim 8, wherein a semiconductor device comprising a first Mos (Kwon col. 1 line 19) transistor having a source region (Kwon fig. 4 # 45, col. 5 line 41), a channel region (Kwon fig.4 # area below gate 44), a drain region (fig.4 # 47, col. 5 line 43), a gate electrode formed on the channel region (fig. 4 # 44, col. 5 line 44), and a drift region formed between the channel region and the drain region (Fig.4 # 43), and a second Mos transistor having a source region, a channel region, a drain region and a gate region formed on the channel region . (Kwon col.4 line 53) ; and wherein the drift region of the first Mos transistor is formed shallowly at least below the gate electrode

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but formed deeply in a neighborhood of the drain region. (Kwon fig. 4) ; and a source / drain region of the second MOS transistor consists of a low concentration source/drain region (Kwon fig. 3 and col. 4 lines 63), a high concentration source-drain region (Kwon col.5 line 4-5) and a middle concentration source/drain region whose concentration is higher than that of the low concentration source/drain region but lower than that of the high concentration source/drain region. (Kwon figs. 5 E to G).

With respect to claim 19, wherein the second conductive type drift region is formed to be adjacent to the first conductive type body region. (Kwon figs. 1,4 etc.).

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 3-4, 9-10 ,17 and 20-32 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kwon et al. (U.S. Patent No. 5,907,173 herein after Kwon) as applied to claims 1-2 and 19 above and further and in view of Blanchard et al. (U.S. Patent No. 5,869,371 herein after Blanchard) .

With respect to claim 3, Kwon describes a semiconductor device including :
a second conductivity type drift region . The limitation, " wherein the second conductivity type drift region is formed by implanting at least two kind second conductivity type impurities which have different diffusion coefficients and at least one

kind first conductivity type impurity which has a diffusion coefficient substantially equal to or larger than the diffusion coefficient of at least one kind second conductivity type impurity such that it is formed by diffusing the second conductivity type impurities in to a deep region by using a difference in the diffusion coefficients and is formed shallowly in a neighborhood of the source region by canceling the second conductivity type impurities by the first conductivity type impurity " in claim 3 is taken to be product-by – process limitations and non limiting. A product-by –process claim is directed to the product per se, no matter how actually made. See *In re Fessman* 180, USPQ 324, 326 (CCPA 1974); *In re Marosi et al.* , 218 USPQ 289, 292 (Fed. Cir. 1983) and *In re Thrope* 227 USPQ 964, 966 (Fed. Cir. 1985).

With respect to claim 4, wherein the second conductivity type drift region is formed by implanting an arsenic ion and a phosphorous ion as the second conductivity type impurities in to an overall surface region serving as the drift region and selectively implanting a boron ion as the first conductivity type impurity only into a region in a neighborhood of the source region.

The limitation," the second conductivity type drift region is formed by implanting an arsenic ion and a phosphorous ion as the second conductivity type impurities in to an overall surface region serving as the drift region and selectively implanting a boron ion as the first conductivity type impurity only into a region in a neighborhood of the source region. " in claim 4 is taken to be product-by –process limitations and non limiting. A product-by –process claim is directed to the product per se, no matter how actually made. See *In re Fessman* 180, USPQ 324, 326 (CCPA 1974); *In re Marosi et al.* , 218

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USPQ 289, 292 (Fed. Cir. 1983) and In re Thrope 227 USPQ 964, 966 (Fed. Cir. 1985).

With respect to claim 9, wherein the a semiconductor device comprising a first Mos (Kwon col. 1 line 19) transistor and a second Mos transistor (Kwon col.4 line 53) formed on the first conductivity type substrate (Kwon fig. 4) wherein the first Mos transistor includes a first conductivity type well region formed in the semiconductor substrate (Kwon fig. 1 p-well), a first gate electrode formed on the first conductivity type well region via a first gate insulating film (Fig.1 # 4-a gate electrode and # 32 gate insulating film), a first conductivity type body region (fig. 1 # 6) formed adjacent to the gate electrode , a second conductivity type source region (fig. 1 # 5) and a channel region formed in the first conductivity body region (fig.1 region below gate 4), and a second conductivity type drain region (Kwon fig. 1 # 7) region formed at a position remote from the first conductivity type body region (Kwon fig.1 # 7) a second conductivity type drift region formed shallowly from the channel region to the drain region, at least below the gate electrode and formed deeply in a neighborhood of the drain region. (Kwon fig.1).

Wherein the second Mos includes : a second conductivity type well region formed in the semiconductor substrate .

Kwon does not specifically mention a second conductivity type well.

However, Blanchard a patent from the same filed of endeavor, describes in fig.5 B etc. a second conductivity type well to provide deep body depths and spacing in relation to the epitaxial layer's depth and doping so that depletion boundaries from the

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body potential will pinch off the channel of the parasitic JFET and thereby protect the channel from high voltages.

Therefore it would have been obvious to one of ordinary skill in the art at the time of the invention to include Blanchard's second conductivity type well in Kwon's method to provide deep body depths and spacing in relation to the epitaxial layer's depth and doping so that depletion boundaries from the body potential will pinch off the channel of the parasitic JFET and thereby protect the channel from high voltages. (Blanchard col. 9 lines 40-50).

The other limitations of claim 9 are : a second gate electrode formed on second conductivity type well region via a second gate insulating film (Blanchard fig. 2 F), and a source / drain region consisting of a low concentration source/drain region formed adjacent to the second gate electrode (Kwon fig. 3 and col. 4 lines 63), a high concentration source-drain region (Kwon col.5 line 4-5) and a middle concentration source/drain region whose concentration is higher than that of the low concentration source/drain region but lower than that of the high concentration source/drain region. (Kwon figs. 5 E to G).

With respect to claim 10, wherein the first Mos transistor consists of an N-Channel LDMOS transistor and the second Mos transistor consists of a P- Channel high breakdown voltage Mos transistor (Kwon col. 4 lines 58- col. 5 lines 45).

With respect to claim 17, wherein the semiconductor device is arranged in plural via a element isolation film and a channel stopper layer is formed under the element

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isolation film. (Blanchard fig. 2g # 134, col. 6 line 14 and fig., 2G # 130, col. 6 line 14-15).

With respect to claims 20 and 21 Kwon describes a semiconductor device in accordance with claim 1, wherein the entire first part of said drift region is located below said gate electrode . (Kwon figure 2)

With respect to claims 22 and 23 Kwon describes a semiconductor device in accordance with claim 1, wherein the dopant concentration of said first part is higher than that of said second part (it is inherent from Kwon figure 2 that the second region is below the first region and therefore the first region has higher concentration because the implanted ions have less distance to travel).

With respect to claims 24 to 32 it is noted that the specification contains no disclosure of either the critical nature of the claimed dimensions or any unexpected results arising therefrom. Where patentability is said to be based upon particular chosen dimension or upon another variable recited in the claim, the Applicant must show that the chosen dimensions/other variables are critical. In re Woodruff, 919 F.,2d 1575, 1578, 16 USPQ 1934, 1936 (Fed. Cir. 1990).

With respect to claim 24, Kwon describes a semiconductor device in accordance with claim 4, wherein the arsenic is implanted in the semiconductor substrate by an accelerating voltage of about 160 KeV at a dose of 3×10^{10} raised to 12 cm^2 . (Kwon col. 6 lines 1-2).

With respect to claim 25 Kwon describes a semiconductor device in accordance with claim 8, wherein the low concentration source/drain region is formed by implanting

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boron in the semiconductor substrate at an accelerating voltage of about 80 KeV at a dose of 8×10^{10} raised to 21 cm^2 . (Kwon col. 6 line 24-26).

With respect to claim 26 Kwon describes a semiconductor device in accordance with claim 8, wherein the middle concentration source/drain region is formed by implanting boron in the semiconductor substrate at an accelerating voltage of about 40 KeV at a dose of 5×10^{10} raised to 13 cm^2 . (Kwon col. 5 lines 63-65)

With respect to claim 27 Kwon describes a semiconductor device in accordance with claim 2, wherein the gate electrode has a thickness of about 2500 Å. (Blanchard col. 4 line 54).

With respect to claim 28. Kwon describes a semiconductor device in accordance with claim 1, wherein the source region is formed by implanting phosphorous in the semiconductor substrate at an accelerating voltage of about 40 KeV at a dose of 3.5×10^{10} raised to 13 cm^2 . (Blanchard col.4 lines 15-17 , kwon col. 5 lines 55-57).

With respect to claim 29 Kwon describes a semiconductor device in accordance with claim 1, wherein the source region is formed by implanting phosphorous in the diffusion region at an accelerating voltage of about 40 KeV at a dose of 3.5×10^{10} raised to 13 cm^2 and by implanting, arsenic at an accelerating voltage of about 80 KeV at a dose of 5×10^{10} raised to 15 cm^2 , and the drain region is formed by implanting arsenic at an accelerating voltage of about 80 KeV at a dose of 5×10^{10} raised to 15 cm^2 . (rejected for same reasons as stated under claims 24-26, 28 above).

With respect to claim 30, Kwon describes a semiconductor device in accordance with claim 1, wherein the drift region has an impurity concentration of about 1×10^{17} cm⁻³. (Kwon col. 4 lines 66-67).

With respect to claim 31, Kwon describes a semiconductor device wherein the size of the element isolation film is 5 to 8 μ m and a distance from the end of the element isolation film to the channel stopper layer is about 2 to 3 μ m. (Kwon col. 4 lines 6-7, lines 64, col. 5 lines 1-3, col. 5 lines 15 -21).

With respect to claim 32, Kwon describes a semiconductor device wherein the channel stopper layer is formed in the semiconductor substrate by implanting boron at an accelerating voltage of about 60 KeV at a dosage of 5×10^{13} cm⁻². (Kwon col. 5 lines 55-59).

Response to Arguments

Applicant's arguments filed 4/22/03 have been fully considered but they are not persuasive. for the following reasons :

Applicants;' first contention that the drift region in the applied Kwon drift region are merely small amount of diffusion that occurs at the edge of any diffusion mask is not persuasive because one of ordinary skill in that art upon seeing the above mentioned references will only conclude that they show and describe well known drift regions.

It is noted that Kwon figs. 1-3 describe Kwon's prior art and figure 4 shows Kwon's invention.

Bulucea is presently not applied as a reference.

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Kwon in figure 2 describes drift region 12 being substantially under the gate 14.

The motivation to combine Kwon and Blanchard was previously given and also restated above.

Therefore all of Applicants' arguments are not persuasive.

THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Steven H. Rao whose telephone number is (703) 3065945. The examiner can normally be reached on 8.00 to 5.00.

The fax phone numbers for the organization where this application or proceeding is assigned are (703) 7463926 for regular communications and (703) 872-9319 for After Final communications.

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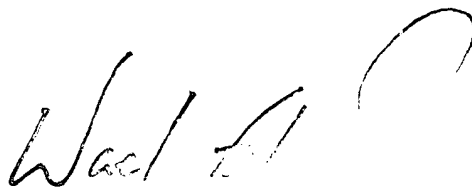
Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 3067722.



Steven H. Rao

Patent Examiner

June 11, 2003.



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